Silicon Carbide Schottky Diode 650 V, 8 A

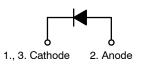
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.



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V _{RRM}	١ _F
650 V	8.0 A

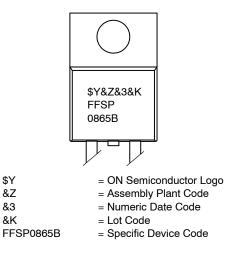


Schottky Diode



TO-220-2LD CASE 340BB

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet

Features • Max Junction Temperature 175°C

- Avalanche Rated 33 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit			
Peak Repetitive Reverse Voltage	Peak Repetitive Reverse Voltage			V		
Single Pulse Avalanche Energy ($I_{L(pk)} = 11.5 \text{ A}, L = 0.5 \text{ mH}, V = 50 \text{ cm}$	E _{AS}	33	mJ			
Continuous Rectified Forward	@ T _C < 147	١ _F	8.0	А		
Current	@ T _C < 135		10.1			
Non-Repetitive Peak Forward Surge Current	T _C = 25°C t _P = 10 μs	I _{FM}	551	A		
	T _C = 150°C t _P = 10 μs		498			
Non-Repetitive Forward Surge Current (Half-Sine Pulse)	T _C = 25°C t _P = 8.3 ms	I _{FSM}	56	A		
Power Dissipation	$T_{C} = 25^{\circ}C$	P _{tot}	73	W		
	T _C = 150°C		12			
Operating Junction and Storage T Range	T _J , T _{stg}	–55 to +175	°C			

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case, Max.	$R_{\theta JC}$	2.05	°C/W

\$Y

&Z

&З

&K

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
ON CHARACTERISTICS						
Forward Voltage	V _F	$I_{F} = 8.0 \text{ A}, \text{ T}_{J} = 25^{\circ}\text{C}$		1.39	1.7	V
		I _F = 8.0 A, T _J = 125°C		1.55	2.0	
		I _F = 8.0 A, T _J = 175°C		1.71	2.4	
Reverse Current	I _R	V_R = 650 V, T_J = 25°C		0.073	40	μA
		$V_{R} = 650 \text{ V}, \text{ T}_{J} = 125^{\circ}\text{C}$		0.24	80	
		$V_{R} = 650 \text{ V}, \text{ T}_{J} = 175^{\circ}\text{C}$		0.48	160	

CHARGES, CAPACITANCES & GATE RESISTANCE

Total Capacitive Charge	Q _C	V _C = 400 V	22	nC
	C _{tot}	V _R = 1 V, f = 100 kHz	336	pF
		V _R = 200 V, f = 100 kHz	39	
		V _R = 400 V, f = 100 kHz	30	

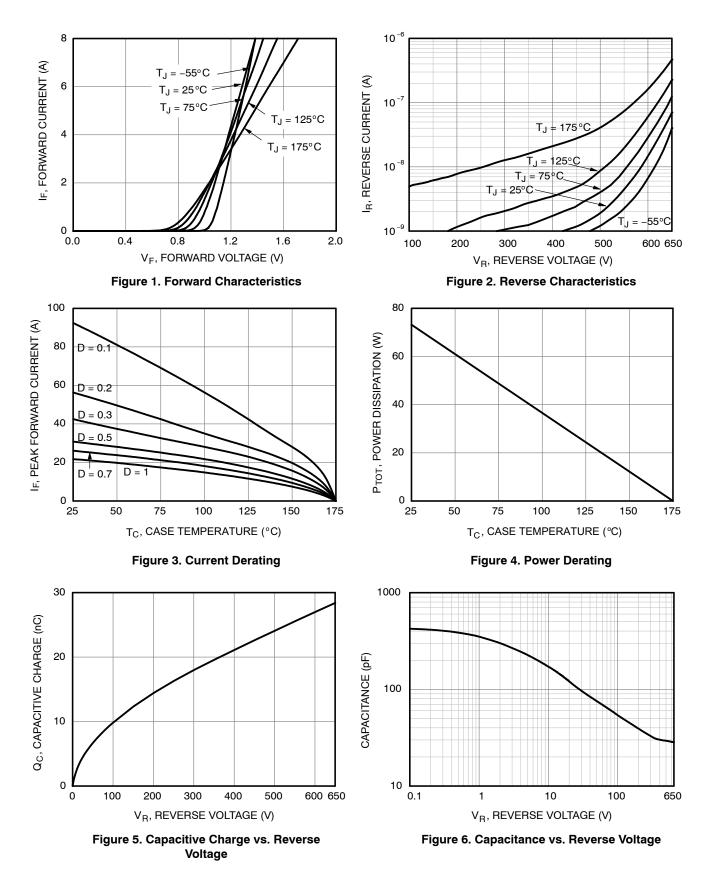
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PACKAGE MARKING AND ORDERING INFORMATION

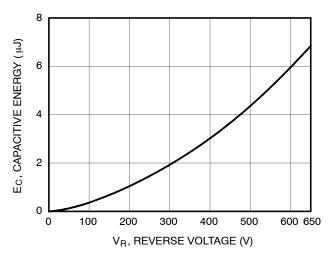
Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSP0865B	FFSP0865B	TO220	Tube	N/A	N/A	50 Units

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS





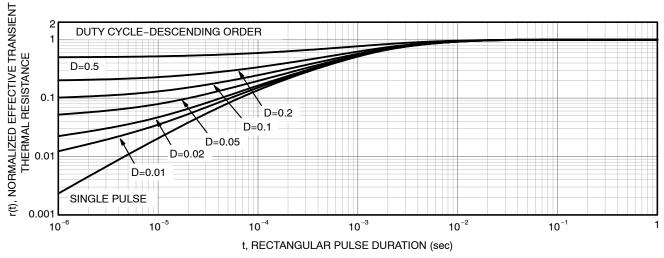
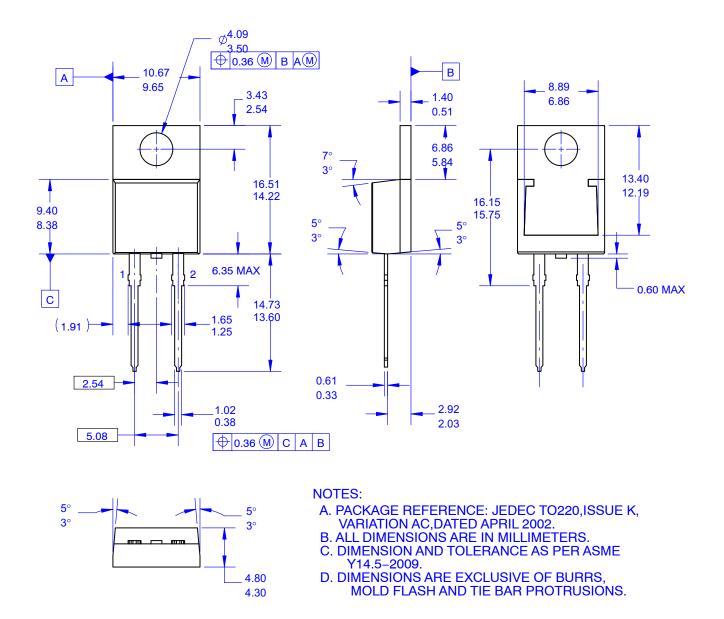


Figure 8. Junction-to-Case Transient Thermal Response



TO-220-2LD CASE 340BB ISSUE O

DATE 31 AUG 2016



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